

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

TMUXHS221NKGR-MS

Product specification

GENERAL DESCRIPTION

The TMUXHS221NKGR-MS is a high bandwidth, fast double-pole double-throw (DPDT) analog switch. Its wide bandwidth and low bit-to-bit skew allow it to pass high-speed differential signals with good signal integrity. Each switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. Its high channel-to-channel crosstalk rejection results in minimal noise interference.

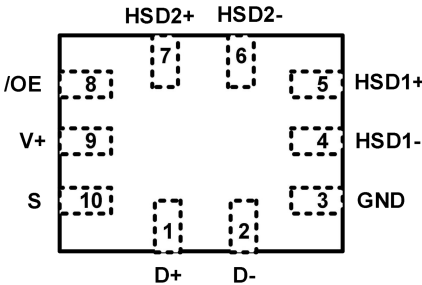
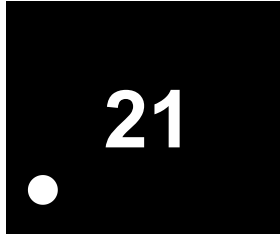
FEATURES

- Supply Range: 1.8 V to 5.5 V
- Rail-to-Rail Signal Range
- On-Resistance Matching: 0.05 Ω (TYP)
- ON-Resistance Flatness: 6.5 Ω (TYP) at 3 V
- High Off Isolation: -32 dB at 250 MHz
- -41 dB (250 MHz) Crosstalk Rejection Reduces
- Break-Before-Make Switching
- -3 dB Bandwidth: 720 MHz
- Operation Temperature Range: -40°C to +125°C

Application

- Cell Phones
- PDAs
- Portable Instrumentation
- Differential Signal Data Routings
- USB 2.0 Signal Routing

Reference News

UFQFN-10(1.4x1.8)	Pin Configuration	MARKING
		

Pin Description

Name	Pin Number		Description
	QA	MA	
V+	9	1	Positive Power Supply
S	10	2	Select Input
D+,D-	1,2	3,4	Data Ports
HSD1+,HSD1-	5,4	7,6	Data Ports 1
HSD2+,HSD2-	7,6	9,8	Data Ports 2
/OE	8	10	Output Enable
GND	3	5	Ground

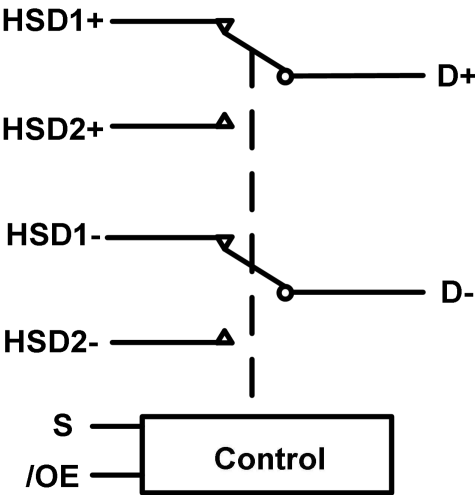
Logic Function Table

/OE	S	HSD1+,HSD1-	HSD2+,HSD2-
0	0	ON	OFF
0	1	OFF	ON
1	X	OFF	OFF

Order information

P/N	PKG	QTY
TMUXHS221NKGR-MS	UFQFN-10(1.4x1.8)	4000PCS

Circuit Diagram



Voltage, Temperature, ESD and Thermal Ratings

Absolute Maximum Ratings

Parameters		Min.	Max.	Unit
V+	Supply Voltage Range	-0.3	6	V
V _{IS}	Analog, Digital Voltage Range	-0.3	(V+)+0.3	V
I _{IN}	Continuous Current HSDn or Dn	-100	+100	mA
I _{peak}	Peak Current HSDn or Dn	-150	+150	mA
T _J	Junction Temperature		150	°C
T _{stg}	Storage Temperature	-65	150	°C

(1) Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

ESD Ratings

ESD			Value	Unit
V(ESD)	Electrostatic Discharge	Human-Body Model (HBM)	5K	V
		Charged-Device Model (CDM)	2K	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	1.8	5.5	V
T _A	Operating Temperature	-40	125	°C

(1) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation.

Thermal Information

Package Type	θ_{JA}	θ_{JC}	Unit
UFQFN-10(1.4x1.8)	120	46	°C/W

Electrical Specifications

DC Electrical Characteristics

V₊=1.8V to 5.5 V, GND=0V, FULL=−40°C to +125°C. Typical values are at T_A=+25°C. (unless otherwise noted)

Parameter	Symbol	Conditions	V ₊	Temp	Min	Typ	Max	Units
Analog Switch								
On-Resistance	R _{ON}	V _{IS} =0V to 0.4V, I _b =10mA, See Fig.8-1.	4.5V	+25°C		4.5	5	Ω
				Full			7	
			3V	+25°C		6.5	7	Ω
				Full			10	
On-Resistance Flatness	R _{FLAT}	V _{IS} =0V to 1.0V, I _b =10mA, See Fig.8-1.	4.5V	+25°C		0.9	1.2	Ω
				Full			1.5	
			3V	+25°C		3.2	3.5	Ω
				Full			4.5	
On-Resistance Matching	ΔR _{ON}	V _{IS} =0V to 0.4V, I _b =10mA, See Fig.8-1.	4.5V	+25°C		0.05	0.1	Ω
				Full			0.15	
			3V	+25°C		0.05	0.1	Ω
				Full			0.15	
Increase In I _{CC} per Control Voltage	I _{CC} T	V _S or V _{IOE} =2.6 V	4.3V	Full			20	μA
Source Off Leakage Current	I _{HSD2(OFF)} I _{HSD1(OFF)}	V _{IS} =5V/ 0.5V, V _D =0.5V/ 5V	5.5V	Full			1	μA
Channel On Leakage Current	I _{HSD2(ON)} I _{HSD1(ON)}	V _{IS} =5V/ 0.5V, V _D =floating	5.5V	Full			1	μA
Digital Control Inputs								
Input High Voltage	V _{IH}		3.3V	Full	1.7			V
Input Low Voltage	V _{IL}		3.3V	Full			0.5	V
Input Leakage current	I _{IN}	V _S , V _{IOE} =0V or V ₊	5.5V	Full			1	μA
Power Requirements								
Power Supply Range	V ₊			Full	1.8		5.5	V
Quiescent Supply Current	I _{CC}	V _S , V _{IOE} =0V or V ₊	5.5V	Full			1	μA

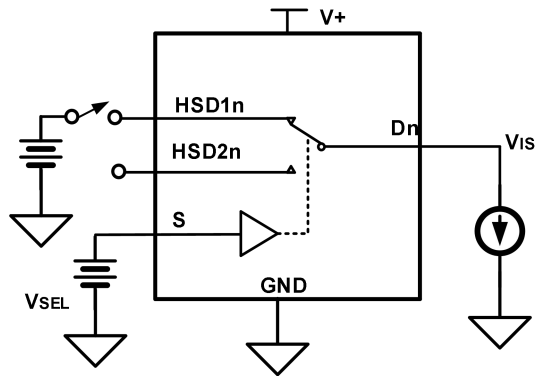
Electrical Specifications(Continued)

Switch And AC Characteristics

V+=1.8V to 5.5 V, GND=0V, FULL=-40°C to +125°C. Typical values are at T_A=+25°C. (unless otherwise noted)

Parameter	Symbol	Conditions	V+	Temp	Min	Typ	Max	Units
Turn-On Time	t _{ON}	V _{IS} =0.8V, R _L =50Ω, C _L =10pF, See Fig.8-2.	5V	+25°C		12		ns
			3.3V	+25°C		14		ns
Turn-Off Time	t _{OFF}	V _{IS} =0.8V, R _L =50Ω, C _L =10pF, See Fig.8-2.	5V	+25°C		6		ns
			3.3V	+25°C		8		ns
Break-Before-Make Delay	t _{BBM}	V _{IS} =0.8V, R _L =50Ω, C _L =10pF, See Fig.8-3.	5V	+25°C		5		ns
			3.3V	+25°C		4		ns
-3 dB Bandwidth	BW	Signal=0dBm, R _L =50Ω C _L =5pF, See Fig.8-6.	5V	+25°C		720		MHz
			3.3V	+25°C		700		MHz
Off-Isolation	OIRR	Signal=0dBm, R _L =50Ω, f=250MHz, See Fig.8-4.	5V	+25°C		-32		dB
			3.3V	+25°C		-32		dB
Non-Adjacent Channel Crosstalk	XTALK	Signal=0dBm, R _L =50Ω, f=250MHz, See Fig.8-5.	5V	+25°C		-41		dB
			3.3V	+25°C		-41		dB
Channel-to-Channel Skew	t _{SKEW}	R _L =50Ω, C _L =10pF	5V	+25°C		0.1		ns
		R _L =50Ω, C _L =10pF	3.3V	+25°C		0.1		ns
Charge Injection	Q	R _G =0Ω, C _L =1nF, See Fig.8-7.	5V	+25°C		6		pC
		R _G =0Ω, C _L =1nF, See Fig.8-7.	3.3V	+25°C		4		pC
On Capacitance	C _{ON}		5V	+25°C		6		pF

Measurement Information

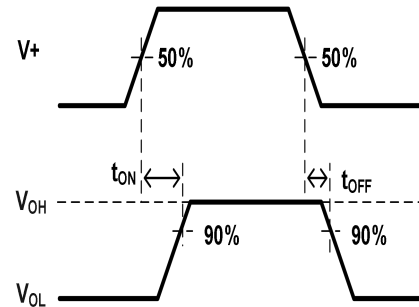
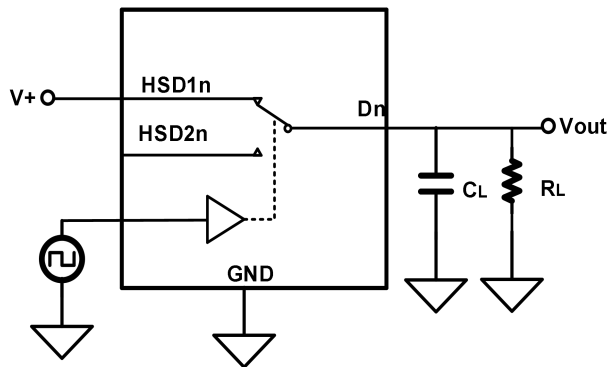


Channel On

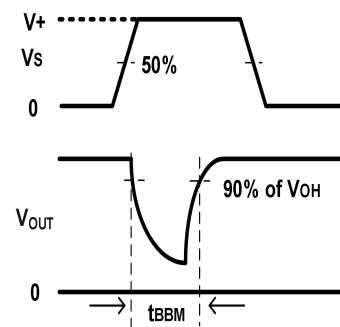
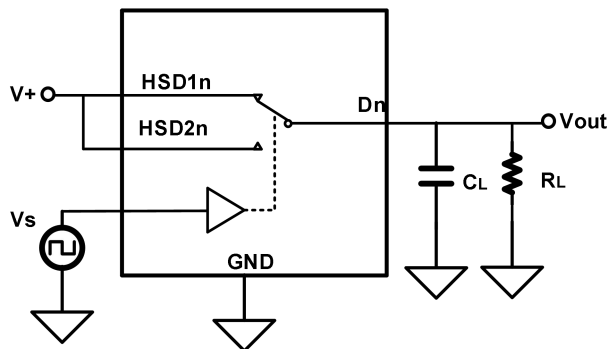
$$R_{ON} = (V_{HSD1n} \text{ or } V_{HSD2n} - V_{DS}) / I_D$$

$V_{SEL} = V_{IH} \text{ or } V_{IL}$

FOM-State Resistance (R_{ON})

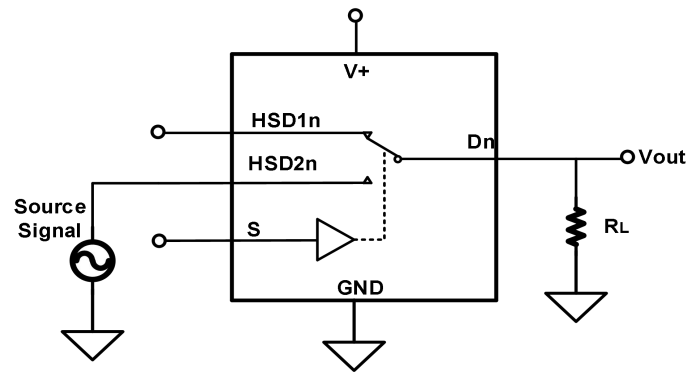


Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

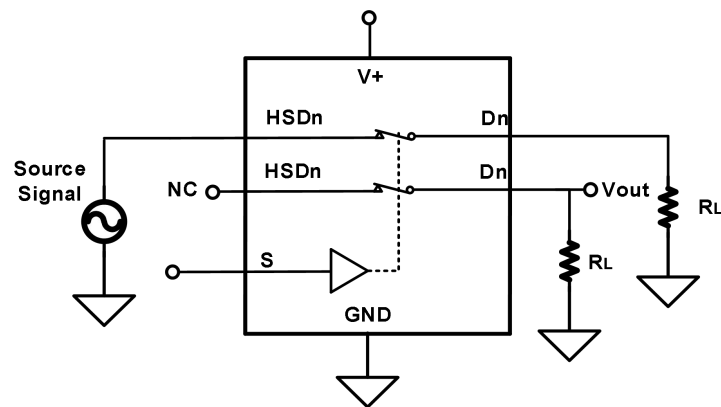


Break-Before-Make Time Delay (t_{BBM})

Measurement Information(Continued)

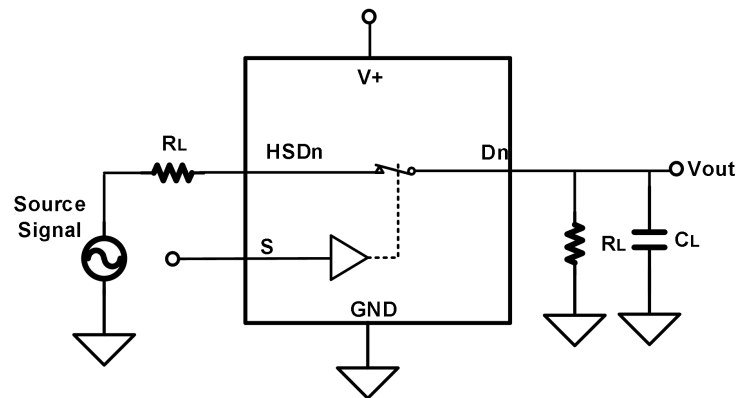


Off Isolation(OIRR)



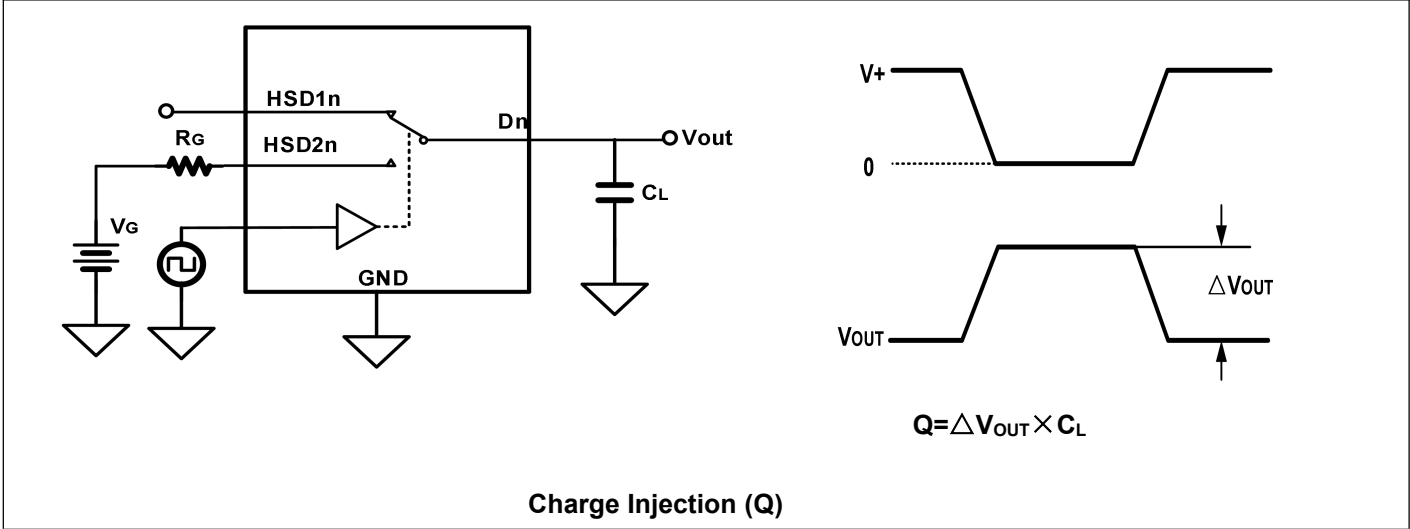
$$\text{Channel To Channel Crosstalk} = -20 \times \log (V_{\text{HSDn}}/V_{\text{OUT}})$$

Channel-to-Channel Crosstalk



-3dB Bandwidth

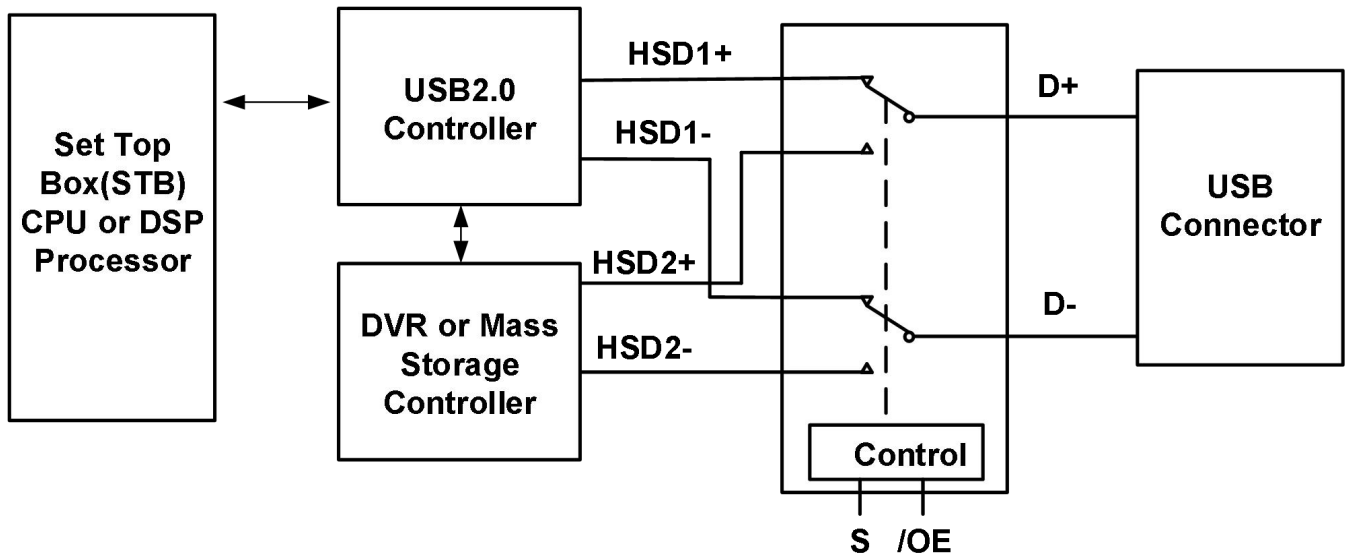
MeasurementInformation(Continued)



Applications Note

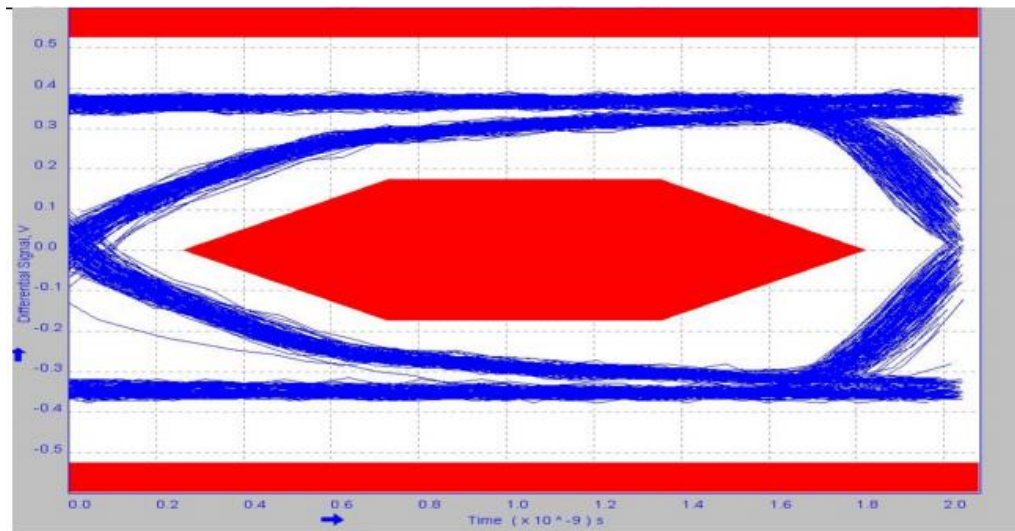
There are many USB applications in which the USB hubs or controllers have a limited number of USB I/Os. The TMUXHS221NKGR-MS solution can effectively expand the limited USB IOs by switching between multiple USB b uses inorder to interface them to a single USB hub or controller. TMUXHS221NKGR-MS can also be used to connect a singlecontroller to two USB connectors or controllers.

Design requirements of the USB 1.0, 1.1, and 2.0 standards should be followed. It is recommended that the digital control pins S and /OE be pulled up to V+ or down to GND to avoid undesired switch positions that could result from the floating pin.

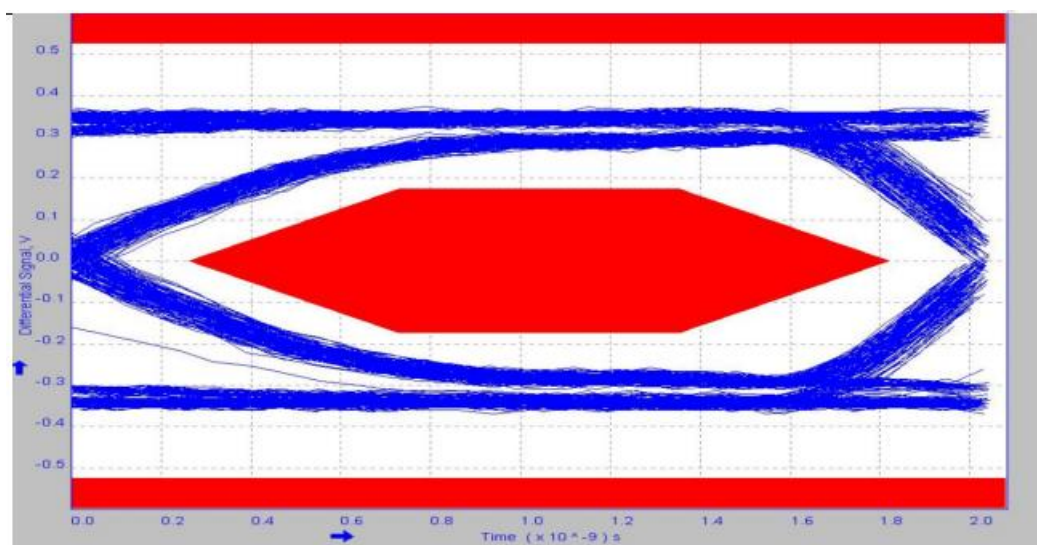


Application Diagram

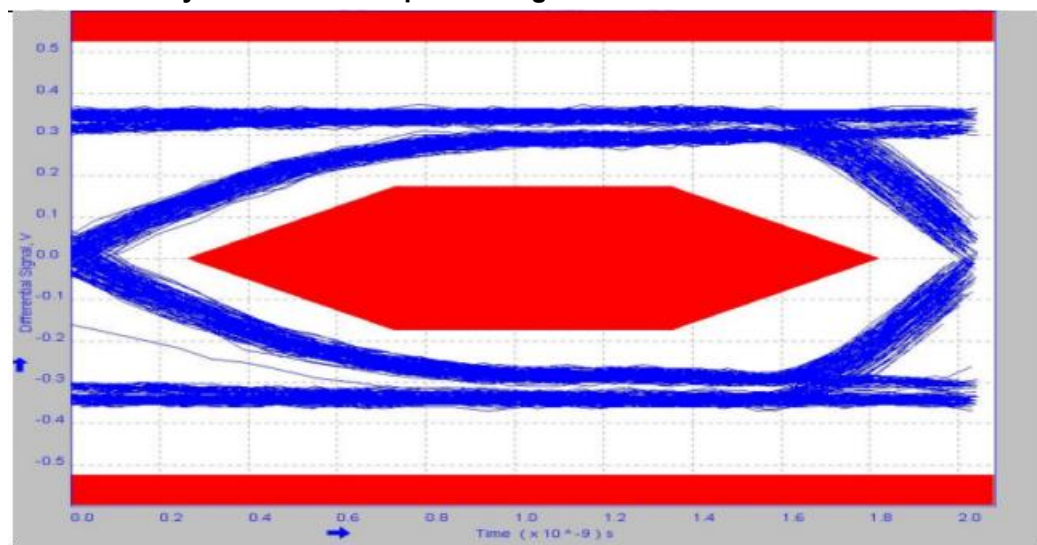
Eye Diagram Measurements



Eye Pattern:480Mbps USB Signal with No Switch (Through Path)



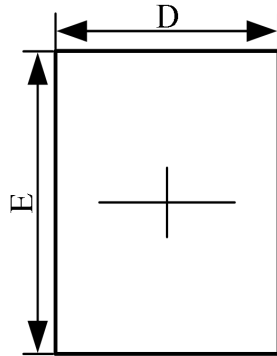
Eye Pattern:480Mbps USB Signal with Switch D+ Path



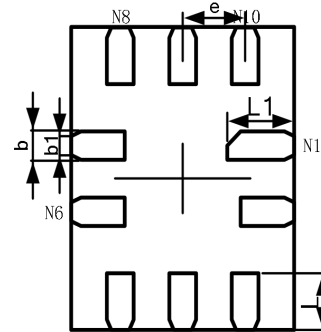
Eye Pattern:480Mbps USB Signal with Switch D- Path

Package Outline Dimension(Continued)

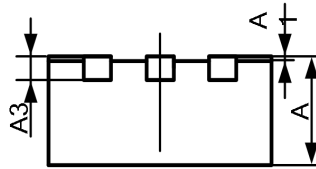
UFQFN-10(1.4x1.8)



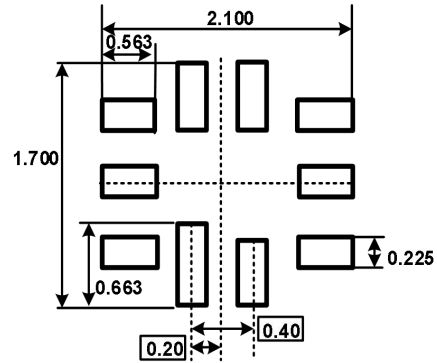
TOP VIEW



BOTTOM VIEW



SIDE VIEW



Recommended Land
Pattern

Symbol	Min	Max	Min	Max
A	0.500	0.600	0.020	0.024
A1	0.000	0.050	0.000	0.002
A3	0.152REF		0.006REF	
D	1.350	1.450	0.053	0.057
E	1.750	1.850	0.069	0.073
D1	—	—	—	—
E1	—	—	—	—
k	—		—	
b	0.150	0.250	0.006	0.010
b1	0.100	0.200	0.004	0.008
e	0.400TYP		0.016TYP	
L	0.350	0.450	0.014	0.018
L1	0.450	0.550	0.018	0.022

Attention

■ Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

■ MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specification of any and all MSKSEMI Semiconductor products described or contained herein.

■ Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

■ MSKSEMI Semiconductor strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

■ Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringement of intellectual property rights or other rights of third parties.

■ Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the MSKSEMI Semiconductor product that you intend to use.